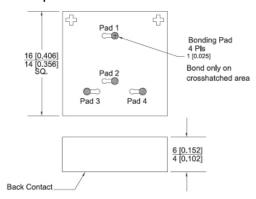
MBD3057-C18 Planar Tunnel Diode

C18 Chip Outline



Dimensions in mils [mm] mils (mm)

Chip assembly

The alloyed junction of the germanium planar diode (or back diode), is sensitive to mechanical pressure and high temperatures. Thus it must be handled as follows (as an example).

Die attach: Epoxy only: less than +125° C cure temperature recommended. Wire bond: +160° C base +160° C capillary temperature, presssure < 20 grams. A wedge bond is done on an offset bonding pad. Bonding should not be done directly over the junction. Bond wire angle should leave small end of pad visually clear to assure junction is not bonded over.

Technical Characteristics

Product Features

Rugged Germanium Planar Construction

Excellent Temperature Stability

No DC Bias Required

Wide Video Bandwidth

MIL-STD-190500 & 883 Qualified

Product Description

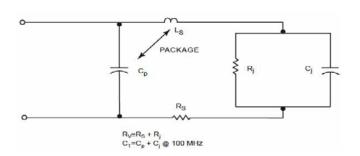
EclipseMDI MBD3057-C18, is a zero-bias, rugged Planar Tunnel Diode constructed with Germanium Planar. This tunnel diode exhibits excellent temperature stability, wide video bandwidth and is MIL STD-190500 & MIL-STD-883C qualified. The MBD3057-C18 is available in chip form.

Maximum Ratings

Storage Temperature	65° to +125°C
Operating Temperature	65° to +110°C
Input Power Handling	+17dBm CW
or 3 ERG spike	
Soldering Temperature	+160° C

	Specifications				
Parameters	Conditions	MIN	Typical	MAX	UNITS
lp		300		400	μΑ
Cj	Vr=Vv, f=100MHz			.30	pF
K[Y]	Pin=-20dBm		500		mV/mW
Rv	R)Load)=10K, f=10GHz		80		Ω Ohms
lp/lv		2.5			
Vr	If=500μA		400		mV
Vf	If=3mA			125	mV

Diode equivalent circuit

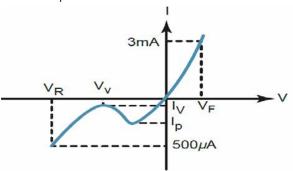


CAUTION: STATIC SENSITIVE DEVICES JUNCTION .0007" THERMOCOMPRESSION WEDGE BOND GOLD BOND WIRE

About EclipseMDI

ECLIPSE Microdevices is located in San Jose, California. ECLIPSE has been developing high performance analog semiconductors for use in wireless radio frequency (RF), microwave, and millimeter wave for commercial and industrial applications. ECLIPSE has formed a strategic alliances - with foundries that features leading state-of-the-art process technologies and with manufacturing facilities for high-volume production of innovative RFIC's.

Back diode parameters



Product Export Classificiation

ECCN: EAR 99 (unless otherwise specified) HTS: 8542330000



